# **Small Signal MOSFET**

-20 V, -200 mA, Dual P-Channel, 1.0 x 1.0 mm SOT-963 Package

#### **Features**

- Dual P-Channel MOSFET
- Offers a Low R<sub>DS(on)</sub> Solution in the Ultra Small 1.0 x 1.0 mm Package
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics.
- This is a Pb-Free Device

#### **Applications**

- High Side Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Equipment

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter			Symbol	Value	Unit	
Drain-to-Source Voltage			V <sub>DSS</sub>	-20	V	
Gate-to-Source Voltag	Gate-to-Source Voltage			±8	V	
Continuous Drain	Steady	$T_A = 25^{\circ}C$		-200		
Current (Note 1)	State	$T_A = 85^{\circ}C$	$I_D$	-140	mA	
	t ≤ 5 s	$T_A = 25^{\circ}C$		-250		
Power Dissipation				-125		
(Note 1)	State	T <sub>A</sub> = 25°C	$P_{D}$		mW	
			-200			
Pulsed Drain Current $t_p = 10 \mu s$			I <sub>DM</sub>	-600	mA	
Operating Junction and Storage Temperature			_T <sub>J</sub> ,	-55 to	°C	
	T <sub>STG</sub>	150				
Source Current (Body Diode) (Note 2)			IS	-200	mA	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface–mounted on FR4 board using the minimum recommended pad size,

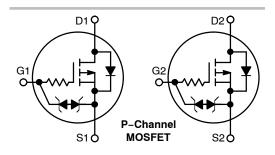
- 2. Pulse Test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%

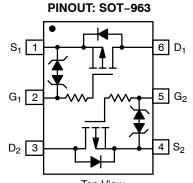


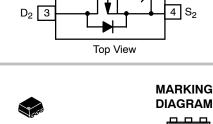
#### ON Semiconductor®

http://onsemi.com

V <sub>(BR)DSS</sub>	V <sub>(BR)DSS</sub> R <sub>DS(ON)</sub> MAX		
-20 V	5.0 Ω @ -4.5 V		
	6.0 Ω @ -2.5 V	-0.2 A	
	7.0 Ω @ –1.8 V	-0.2 A	
	10 Ω @ -1.5 V		







= Specific Device Code 4

SOT-963 CASE 527AD

> = Date Code Μ = Pb-Free Package

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 3)	$R_{ heta JA}$	1000	°C/W
Junction-to-Ambient - t = 5 s (Note 3)		600	

<sup>3.</sup> Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS	•						
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$		-20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = -5.0 \text{ V}$	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = -5.0 V T <sub>J</sub> = 25°C			-50	
		$V_{GS} = 0 \text{ V}, V_{DS} = -5.0 \text{ V}$	T <sub>J</sub> = 85°C			-100	nA
		V <sub>GS</sub> = 0 V, V <sub>DS</sub> = -16 V	T <sub>J</sub> = 25°C			-200	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5.0 \text{ V}$				±100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D = -2$	250 μΑ	-0.4		-1.0	V
Drain-to-Source On Resistance	R <sub>DS(ON)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -100 \text{ mA}$ $V_{GS} = -2.5 \text{ V}, I_D = -50 \text{ mA}$ $V_{GS} = -1.8 \text{ V}, I_D = -20 \text{ mA}$ $V_{GS} = -1.5 \text{ V}, I_D = -10 \text{ mA}$			2.0	5.0	Ω
					2.6	6.0	
					3.4	7.0	
					4.0	10	
		$V_{GS} = -1.2 \text{ V}, I_D = -1.0 \text{ mA}$			6.0		
Forward Transconductance	9FS	$V_{DS} = -5.0 \text{ V}, I_D = -125 \text{ mA}$			0.35		S
Source-Drain Diode Voltage	$V_{SD}$	$V_{GS} = 0 \text{ V, } I_{S} = -10 \text{ mA}$			-0.6	-1.0	V
CHARGES, CAPACITANCES AND GATE	RESISTANCE						
Input Capacitance	C <sub>ISS</sub>				13.5		
Output Capacitance	C <sub>OSS</sub>	f = 1 MHz, V <sub>GS</sub> = 0 V V <sub>DS</sub> = -15 V			3.8		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>				2.0		
SWITCHING CHARACTERISTICS, $V_{GS} =$	4.5 V (Note 4)						
Turn-On Delay Time	t <sub>d(ON)</sub>	$V_{GS} = -4.5 \text{ V}, V_{DD} = -15 \text{ V},$ $I_{D} = -200 \text{ mA}, R_{G} = 2.0 \Omega$			26		- ns
Rise Time	t <sub>r</sub>				46		
Turn-Off Delay Time	t <sub>d(OFF)</sub>				196		
Fall Time	t <sub>f</sub>				145		

<sup>4.</sup> Switching characteristics are independent of operating junction temperatures

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>		
NTUD3171PZT5G	SOT-963 (Pb-Free)	8000 / Tape & Reel		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **TYPICAL CHARACTERISTICS**

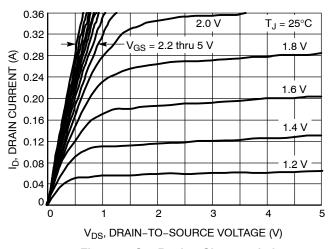


Figure 1. On-Region Characteristics

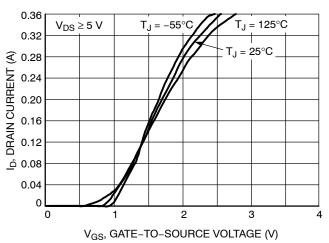


Figure 2. Transfer Characteristics

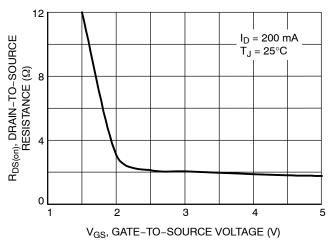


Figure 3. On-Resistance vs. Gate Voltage

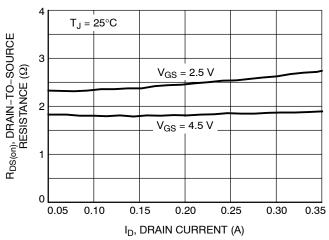


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

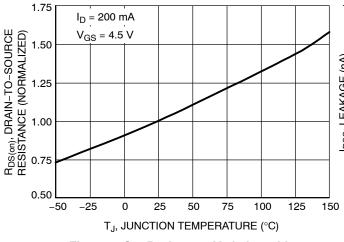


Figure 5. On–Resistance Variation with Temperature

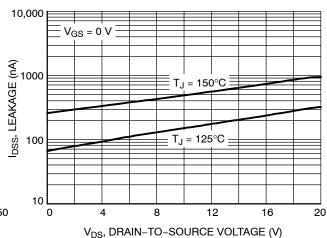
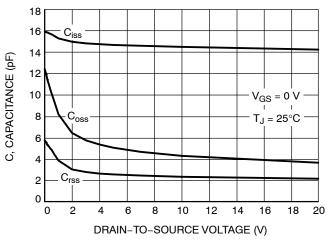


Figure 6. Drain-to-Source Leakage Current vs. Voltage

## **TYPICAL CHARACTERISTICS**



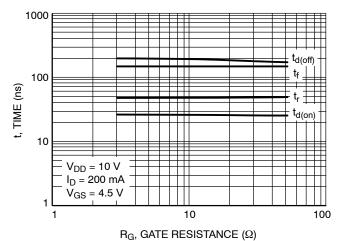


Figure 7. Capacitance Variation

Figure 8. Resistive Switching Time Variation vs. Gate Resistance

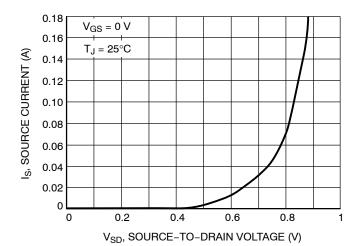
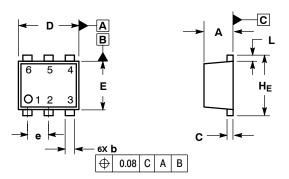


Figure 9. Diode Forward Voltage vs. Current

#### PACKAGE DIMENSIONS

#### SOT-963 CASE 527AD-01 ISSUE D

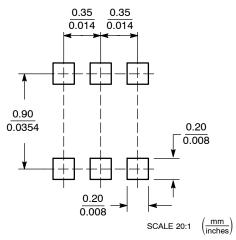


- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- T14-3M, 1962.

  CONTROLLING DIMENSION: MILLIMETERS
  MAXIMUM LEAD THICKNESS INCLUDES LEAD
  FINISH THICKNESS. MINIMUM LEAD THICKNESS
  IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	MON	MAX
Α	0.34	0.37	0.40			
b	0.10	0.15	0.20	0.004	0.006	0.008
С	0.07	0.12	0.17	0.003	0.005	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
E	0.75	0.80	0.85	0.03	0.032	0.034
е	0.35 BSC		(	0.014 BS	S	
L	0.05	0.10	0.15	0.002	0.004	0.006
HE	0.95	1.00	1.05	0.037	0.039	0.041

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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